

3.2 Ω , 8-Channel, ± 15 V, +12 V, ± 5 V Precision Multiplexers

DESCRIPTION

The DG1408 is a precision analog multiplexer comprising eight single-ended channels. Built on a new CMOS process, the Vishay Siliconix DG1408 offers low on-resistance of 3.2 Ω . The low and flat resistance over the full signal range provides excellent linearity and low signal distortion. The new CMOS platform also ensures ultra low power dissipation, minimized parasitic capacitance, and low charge injection.

The DG1408 can operate from either a single 4.5 V to 24 V power supply, or from dual ± 4.5 V to ± 15 V power supplies. The DG1408 connects one of eight inputs to a common output as determined by a 3-bit binary address (A0, A1, A2). Break-before-make switching action protects against momentary crosstalk between adjacent channels. The part does not require a VL logic supply, while all digital inputs have 0.8 V and 2 V logic thresholds to ensure low-voltage TTL / CMOS compatibility. Together with the compact package, these make the part a great fit for battery operated systems.

The DG1408 on channel conducts signal equally well in both directions. In the off state each channel blocks voltages up to the power supply rails. An enable (EN) function allows the user to reset the multiplexer / demultiplexer to all switches off for stacking several devices.

The advance performance of low insertion loss and low distortion make the device ideal for signal switching and relay replacement in a wide range of applications.

DG1408 is available in RoHS-compliant, halogen-free QFN16, 4 mm x 4 mm package.

FEATURES

- 35 V supply max. rating
- 3.2 Ω typical and 4.7 Ω max. on-resistance at 25 $^{\circ}\text{C}$
- 0.5 Ω on-resistance flatness
- Channel to channel on-resistance match: 0.2 Ω
- Up to 250 mA continuous current
- Supports single and dual supply operation
- Fully specified at ± 15 V, +12 V, and ± 5 V
- Integrated VL supply
- Low voltage logic compatible inputs, $V_{IH} = 2$ V, $V_{IL} = 0.8$ V
- BBM (break-before-make switching)
- Low parasitic capacitance:
DG1408, $C_{S(off)} = 23$ pF, $C_{D(on)} = 121$ pF
- Rail to rail signal handling
- QFN16, 4 mm x 4 mm packages
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

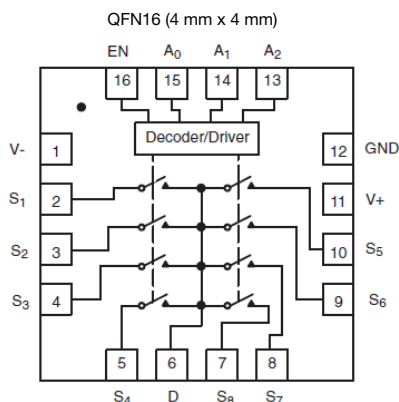
BENEFITS

- Low insertion loss
- Low distortion
- Low power consumption
- Compact solution
- Low charge injection over the full signal range

APPLICATIONS

- Medical and healthcare equipment
- Data acquisition system
- Industrial control and automation
- Test and measurement equipment
- Communication systems
- Battery powered systems
- Sample and hold circuits
- Audio and video signal switching
- Relay replacement

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE - DG1408

A2	A1	A0	EN	ON SWITCH
X	X	X	0	None
0	0	0	1	1
0	0	1	1	2
0	1	0	1	3
0	1	1	1	4
1	0	0	1	5
1	0	1	1	6
1	1	0	1	7
1	1	1	1	8

Note

- QFN exposed pad tied to V-

**ORDERING INFORMATION**

PART	CONFIGURATION	TEMPERATURE RANGE	PACKAGE	ORDERING PART NUMBER
DG1408	8:1 MUX	-40 °C to +125 °C	QFN (4 mm x 4 mm) 16L (variation 2)	DG1408EN-T1-GE4

ABSOLUTE MAXIMUM RATINGS

ELECTRICAL PARAMETER	CONDITIONS	LIMITS	UNIT
V+	Reference to GND	-0.3 V to +25 V	V
V-	Reference to GND	+0.3 V to -25 V	
V+ to V-		+35	
Analog Inputs (S or D)		V- (-0.3 V) to V+ (+0.3 V)	
Digital Inputs		GND (-0.3 V) to V+ (+0.3 V)	
Maximum Continuous Switch Current	QFN (4 mm x 4 mm) 16L, T _A = 25 °C	250	mA
	QFN (4 mm x 4 mm) 16L, T _A = 125 °C	100	
Maximum Pulse Switch Current	Pulse at 1 ms, 10 % duty cycle	500	
Thermal Resistance	QFN (4 mm x 4 mm) 16L	32	°C/W
Temperature			
Operating Temperature		-40 to 125	°C
Max. Operating Junction Temperature		150	
Storage Temperature		-65 to 150	

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING RANGE

ELECTRICAL	MINIMUM	MAXIMUM	UNIT
Single Supply (V+)	4.5	24	V
Dual Supplies (V+ and V-)	± 4.5	± 16.5	

**ELECTRICAL CHARACTERISTICS**

PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED V ₊ = 15 V, V ₋ = -15 V V _{AX} , V _{EN} = 2 V, 0.8 V	+25 °C	-40 °C to +85 °C	-40 °C to +125 °C	MIN./TYP. /MAX.	UNIT
Analog Switch							
Analog Signal Range	V _{ANALOG}		V ₋ to V ₊			-	V
Drain-Source On-Resistance	R _{DS(on)}	V _S = ± 10 V, I _S = -10 mA, V ₊ = +13.5 V, V ₋ = -13.5 V	3.2	-	-	Typ.	Ω
			4.7	5.7	6.7	Max.	
On-Resistance Flatness	R _{flat(on)}		0.5	-	-	Typ.	
			0.7	0.8	0.9	Max.	
On-Resistance Matching	ΔR _{DS(on)}		0.2	-	-	Typ.	Ω
			0.7	0.8	1	Max.	
Source Off Leakage Current	I _{S(off)}	V ₊ = +16.5 V, V ₋ = -16.5 V, V _S = ± 10 V, V _D = ± 10 V	± 0.02	-	-	Typ.	nA
			± 0.2	± 0.8	± 10	Max.	
Drain Off Leakage Current	I _{D(off)}		± 0.06	-	-	Typ.	
			± 0.3	± 3	± 20	Max.	
Drain On Leakage Current	I _{D(on)}	V ₊ = +16.5 V, V ₋ = -16.5 V, V _S = V _D = ± 10 V	± 0.08	-	-	Typ.	nA
			± 1	± 4	± 35	Max.	
Digital Control							
Input, High Voltage	V _{INH}		-	-	2	Min.	V
Input, Low Voltage	V _{INL}		-	-	0.8	Max.	
Input Leakage	I _{IN}	V _{IN} = V _{GND} or V ₊	0.005	-	-	Typ.	μA
			-	-	± 0.1	Max.	
Digital Input Capacitance	C _{IN}		3.5	-	-	Typ.	pF
Dynamic Characteristics							
Transition Time	t _{TRANS}	V _{S1} = +10 V / -10 V, V _{S8} = -10 V / +10 V, R _L = 100 Ω, C _L = 35 pF	140	-	-	Typ.	ns
			180	220	250	Min.	
Break-Before-Make Time	t _{OPEN}	V _{S1} = V _{S8} = 10 V, R _L = 100 Ω, C _L = 35 pF	50	-	-	Typ.	
			-	-	10	Min.	
Enable Turn-On Time	t _{ON(EN)}	V _{S1} = 10 V, V _{S2} - V _{S8} = 0 V, R _L = 300 Ω, C _L = 35 pF	125	-	-	Typ.	
			150	170	190	Max.	
Enable Turn-Off Time	t _{OFF(EN)}		100	-	-	Typ.	
			120	140	160	Max.	
Charge Injection	Q _{INJ}	C _{INJ} = 1 nF, R _{GEN} = 0 Ω, V _S = 0 V	120	-	-	Typ.	pC
Off Isolation	OIRR	C _L = 5 pF, R _L = 50 Ω, 1 MHz	-62	-	-	Typ.	dB
Cross Talk	X _{TALK}		-66	-	-	Typ.	
Total Harmonic Distortion	THD	R _L = 100 Ω, 15 V _{p-p} , f = 20 Hz to 20 kHz	0.02	-	-	Typ.	%
-3dB, Bandwidth	BW	R _L = 50 Ω	60	-	-	Typ.	MHz
Source Off Capacitance	C _{S(off)}	f = 1 MHz, V _S = 0 V	23	-	-	Typ.	pF
Drain Off Capacitance	C _{D(off)}		76	-	-	Typ.	
Drain On Capacitance	C _{D(on)}		121	-	-	Typ.	
Power Supply							
Power Supply Range		GND = 0 V	± 4.5 / ± 16.5			Min./Max.	V
Positive Supply Current	I ₊	V _{AX} , V _{EN} = 0 V, V ₊ , V ₊ = +16.5 V, V ₋ = -16.5 V	17	14.5	14	Typ.	μA
			-	-	30	Max.	
		V _{AX} , V _{EN} = 5 V, V ₊ = +16.5 V, V ₋ = -16.5 V	17	14.5	14	Typ.	
			-	-	50	Max.	
Negative Supply Current	I ₋	V _{AX} , V _{EN} = 0 V, V ₊ , V ₊ = +16.5 V, V ₋ = -16.5 V	0.002	0.22	0.4	Typ.	μA
			-	-	1	Max.	

**ELECTRICAL CHARACTERISTICS**

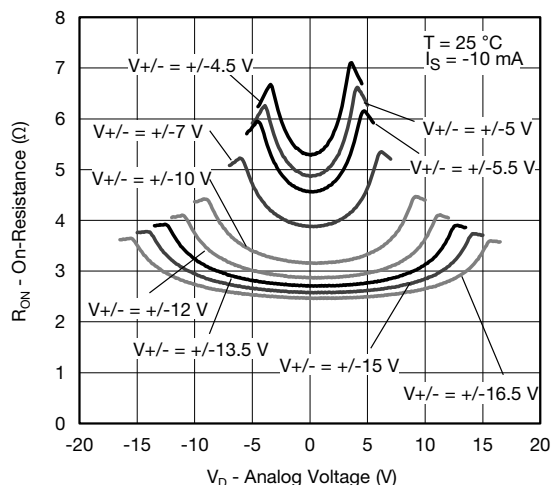
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED V ₊ = 12 V, V ₋ = 0 V V _{AX} , V _{EN} = 2 V, 0.8 V	+25 °C	-40 °C to +85 °C	-40 °C to +125 °C	MIN./TYP./ MAX.	UNIT
Analog Switch							
Analog Signal Range	V _{ANALOG}		0 to V ₊			-	V
Drain-Source On-Resistance	R _{DS(on)}	V _S = 0 V / 10 V, I _S = -10 mA, V ₊ = +10.8 V, V ₋ = 0 V	5.5	-	-	Typ.	Ω
			8	9	11	Max.	
On-Resistance Flatness	R _{flat(on)}		1	-	-	Typ.	
			2	2.5	3	Max.	
On-Resistance Matching	ΔR _{DS(on)}		0.2	-	-	Typ.	
			0.7	0.8	1	Max.	
Source Off Leakage Current	I _{S(off)}	V ₊ = +13.2 V, V ₋ = 0 V, V _S = 1 V / 10 V, V _D = 10 V / 1 V	± 0.02	-	-	Typ.	nA
			± 0.2	± 0.6	± 5	Max.	
Drain Off Leakage Current	I _{D(off)}		± 0.02	-	-	Typ.	
			± 0.3	± 2	± 20	Max.	
Drain On Leakage Current	I _{D(on)}	V _S = V _D = 1 V / 10 V	± 0.05	-	-	Typ.	
			± 0.6	± 3	± 20	Max.	
Digital Control							
Input, High Voltage	V _{INH}		-	-	2	Min.	V
Input, Low Voltage	V _{INL}		-	-	0.8	Max.	
Input Leakage	I _{IN}	V _{IN} = V _{GND} or V ₊	0.001	-	-	Typ.	μA
			-	-	± 0.1	Max.	
Digital Input Capacitance	C _{IN}		3.5	-	-	Typ.	pF
Dynamic Characteristics							
Transition Time	t _{TRANS}	V _{S1} = 8 V / 0 V, V _{S8} = 0 V / 8 V, R _L = 100 Ω, C _L = 35 pF	160	-	-	Typ.	ns
			240	290	330	Min.	
Break-Before-Make Time	t _{OPEN}	V _{S1} = V _{S8} = 8 V, R _L = 100 Ω, C _L = 35 pF	95	-	-	Typ.	
			-	-	10	Min.	
Enable Turn-On Time	t _{ON(EN)}	V _{S1} = 8 V, V _{S2} - V _{S8} = 0 V, R _L = 100 Ω, C _L = 35 pF	190	-	-	Typ.	
			250	290	330	Max.	
Enable Turn-Off Time	t _{OFF(EN)}		105	-	-	Typ.	
			160	200	240	Max.	
Charge Injection	Q _{INj}	C _{INJ} = 1 nF, R _{GEN} = 0 Ω, V _S = 6 V	22	-	-	Typ.	pC
Off Isolation	OIRR	C _L = 5 pF, R _L = 50 Ω, 1 MHz	-62	-	-	Typ.	dB
Cross Talk	X _{TALK}		-65	-	-	Typ.	
Total Harmonic Distortion	THD	R _L = 100 Ω, 6 V _{p-p} , f = 20 Hz to 20 kHz	0.05	-	-	Typ.	%
-3dB, Bandwidth	BW	R _L = 50 Ω	55	-	-	Typ.	MHz
Source Off Capacitance	C _{S(off)}	f = 1 MHz, V _S = 6 V	27	-	-	Typ.	pF
Drain Off Capacitance	C _{D(off)}		100	-	-	Typ.	
Drain On Capacitance	C _{D(on)}		146	-	-	Typ.	
Power Supply							
Power Supply Range		GND = 0 V, V ₋ = 0 V	4.5 / 24			Min./Max.	V
Positive Supply Current	I ₊	V _{AX} , V _{EN} = 0 V, V ₊ , V ₊ = +13.2 V, V ₋ = 0 V	11	9.5	9	Typ.	μA
			-	-	20	Max.	
		V _{AX} , V _{EN} = 5 V, V ₊ = 13.2 V, V ₋ = 0 V	11	9.5	9	Typ.	
			-	-	40	Max.	

**ELECTRICAL CHARACTERISTICS**

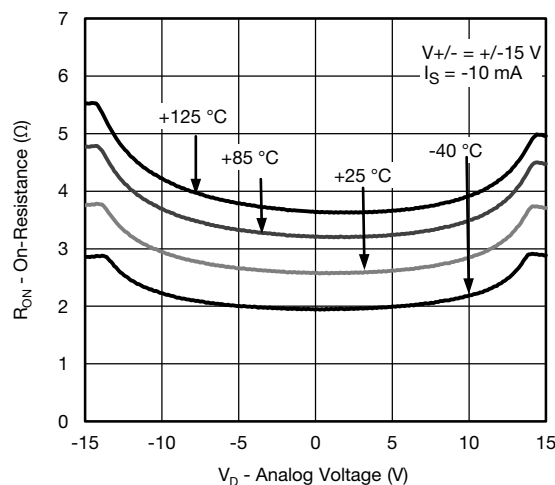
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED V ₊ = 5 V, V ₋ = -5 V V _{AX} , V _{EN} = 2 V, 0.8 V	+25 °C	-40 °C to +85 °C	-40 °C to +125 °C	MIN./TYP./ MAX.	UNIT
Analog Switch							
Analog Signal Range	V _{ANALOG}		V ₋ to V ₊			-	V
Drain-Source On-Resistance	R _{DS(on)}	V _S = ± 3.5 V, I _S = -10 mA, V ₊ = +4.5 V, V ₋ = -4.5 V	7	-	-	Typ.	Ω
			9	10	12	Max.	
On-Resistance Flatness	R _{flat(on)}		1.5	-	-	Typ.	
			2.5	3	3	Max.	
On-Resistance Matching	ΔR _{DS(on)}		0.2	-	-	Typ.	
			0.7	0.8	1	Max.	
Source Off Leakage Current	I _{S(off)}	V ₊ = +5.5 V, V ₋ = -5.5 V, V _S = ± 4.5 V, V _D = ± 4.5 V	± 0.01	-	-	Typ.	nA
			± 0.2	± 0.8	± 10	Max.	
Drain Off Leakage Current	I _{D(off)}		± 0.02	-	-	Typ.	
			± 0.3	± 3	± 20	Max.	
Drain On Leakage Current	I _{D(on)}	V ₊ = +5.5 V, V ₋ = -5.5 V, V _S = V _D = ± 4.5 V	± 0.05	-	-	Typ.	
			± 1	± 4	± 35	Max.	
Digital Control							
Input, High Voltage	V _{INH}		-	-	2	Min.	V
Input, Low Voltage	V _{INL}		-	-	0.8	Max.	
Input Leakage	I _{IN}	V _{IN} = V _{GND} or V ₊	0.001	-	-	Typ.	μA
			-	-	± 0.1	Max.	
Digital Input Capacitance	C _{IN}		3.5	-	-	Typ.	pF
Dynamic Characteristics							
Transition Time	t _{TRANS}	V _{S1} = +3 V / -3 V, V _{S8} = -3 V / +3 V, R _L = 100 Ω, C _L = 35 pF	275	-	-	Typ.	ns
			350	400	440	Min.	
Break-Before-Make Time	t _{OPEN}	V _{S1} = V _{S8} = 3 V, R _L = 100 Ω, C _L = 35 pF	110	-	-	Typ.	
			-	-	10	Min.	
Enable Turn-On Time	t _{ON(EN)}	V _{S1} = 3 V, V _{S2} - V _{S8} = 0 V, R _L = 100 Ω, C _L = 35 pF	245	-	-	Typ.	
			290	350	390	Max.	
Enable Turn-Off Time	t _{OFF(EN)}		185	-	-	Typ.	
			240	300	340	Max.	
Charge Injection	Q _{INJ}	C _{INJ} = 1 nF, R _{GEN} = 0 Ω, V _S = 0 V	16	-	-	Typ.	pC
Off Isolation	OIRR	C _L = 5 pF, R _L = 50 Ω, 1 MHz	-62	-	-	Typ.	dB
Cross Talk	X _{TALK}		-66	-	-	Typ.	
Total Harmonic Distortion	THD	R _L = 100 Ω, 5 V _{p-p} , f = 20 Hz to 20 kHz	0.065	-	-	Typ.	%
-3dB, Bandwidth	BW	R _L = 50 Ω	60	-	-	Typ.	MHz
Source Off Capacitance	C _{S(off)}	f = 1 MHz, V _S = 0 V	27	-	-	Typ.	pF
Drain Off Capacitance	C _{D(off)}		105	-	-	Typ.	
Drain On Capacitance	C _{D(on)}		150	-	-	Typ.	
Power Supply							
Power Supply Range		GND = 0 V	± 4.5 / ± 16.5			Min./Max.	V
Positive Supply Current	I ₊	V _{AX} , V _{EN} = 0 V, V ₊ , V ₊ = +5.5 V, V ₋ = -5.5 V	0.5	0.7	1	Typ.	μA
			-	-	20	Max.	
		V _{AX} , V _{EN} = 3 V, V ₊ = +5.5 V, V ₋ = -5.5 V	0.7	1.3	2	Typ.	
			-	-	50	Max.	
Negative Supply Current	I ₋	V _{AX} , V _{EN} = 0 V, V ₊ , V ₊ = +5.5 V, V ₋ = -5.5 V	0.0002	0.013	0.026	Typ.	
			-	-	1	Max.	



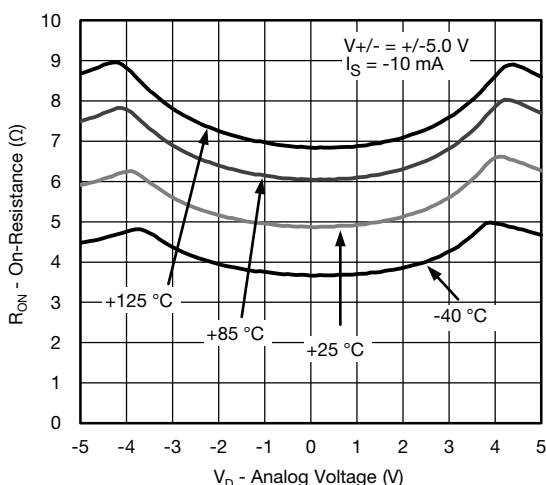
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



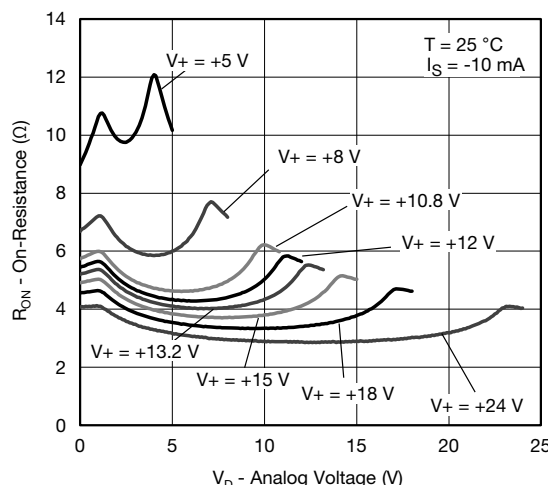
On-Resistance vs. Analog Voltage



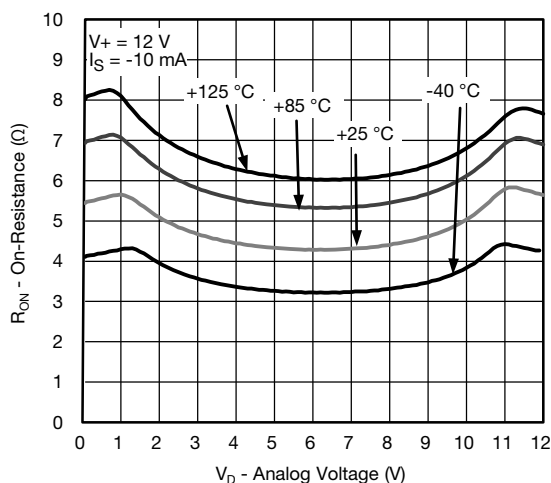
On-Resistance vs. Analog Voltage



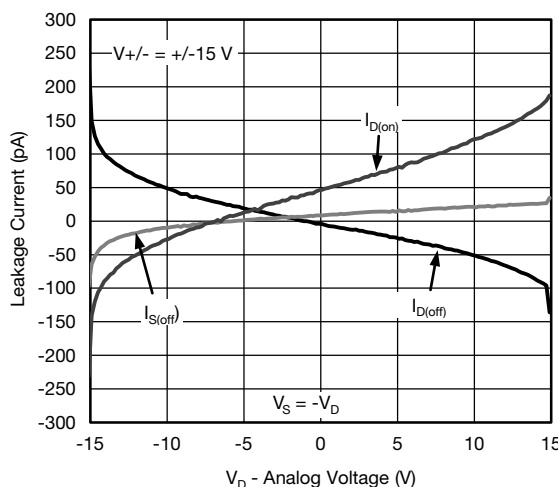
On-Resistance vs. Analog Voltage



On-Resistance vs. Analog Voltage



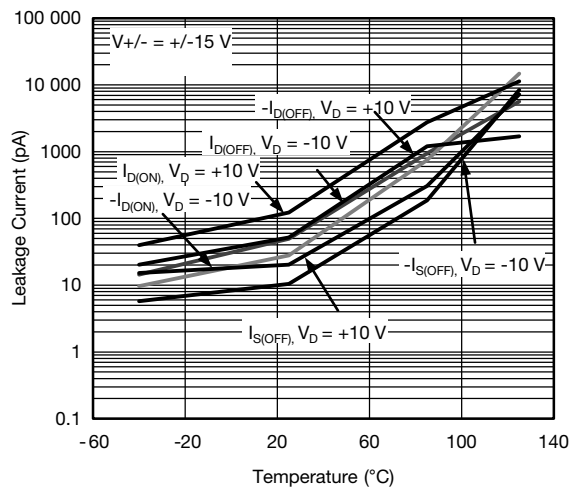
On-Resistance vs. Analog Voltage



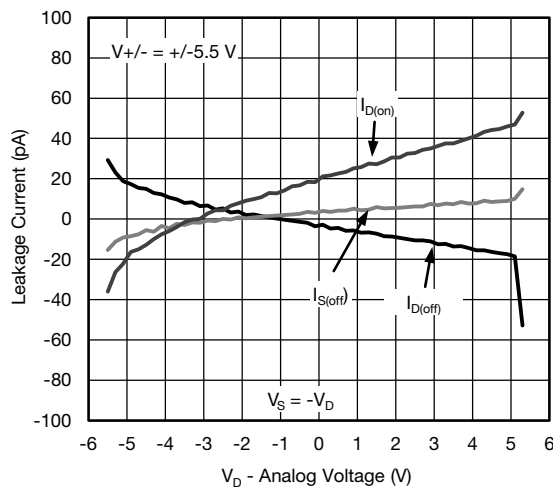
Leakage Current vs. Analog Voltage



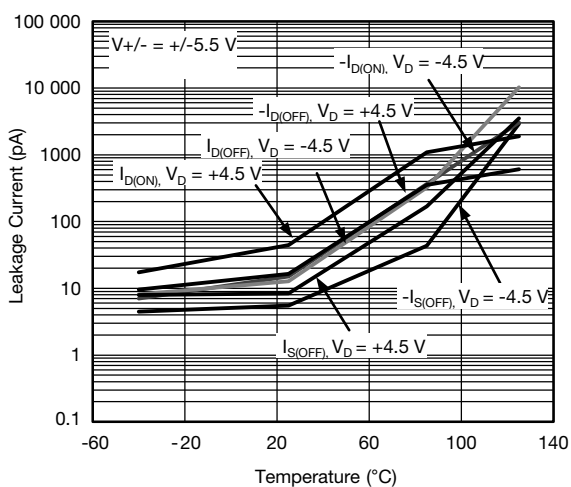
TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)



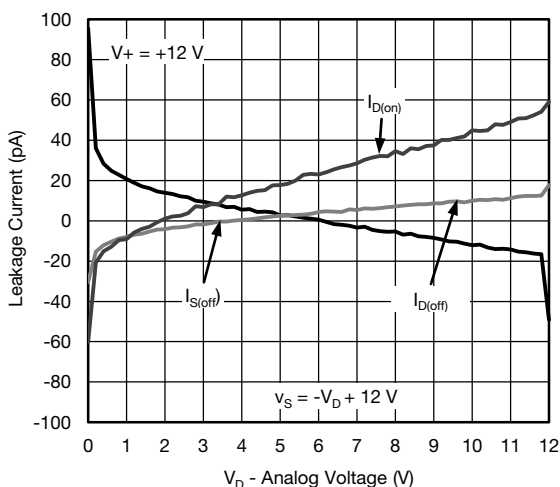
Leakage Current vs. Temperature



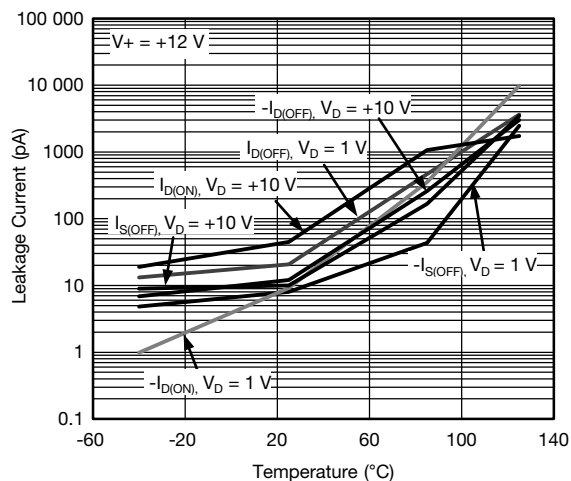
Leakage Current vs. Temperature



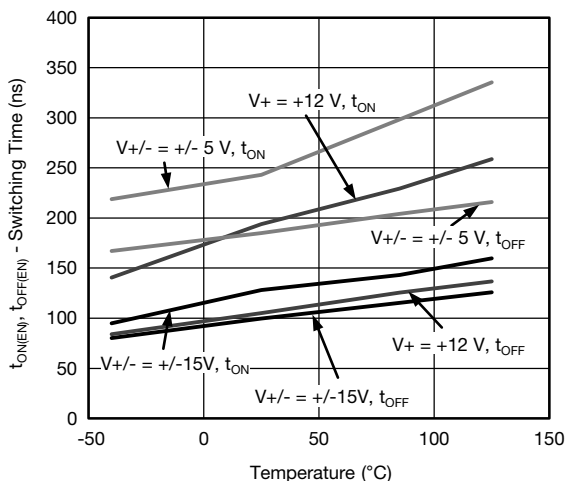
Leakage Current vs. Temperature



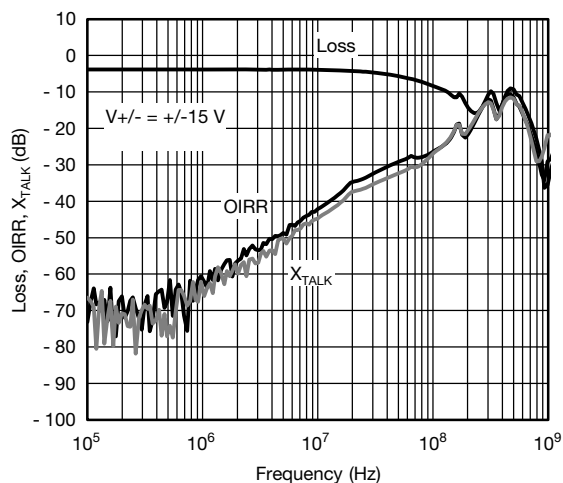
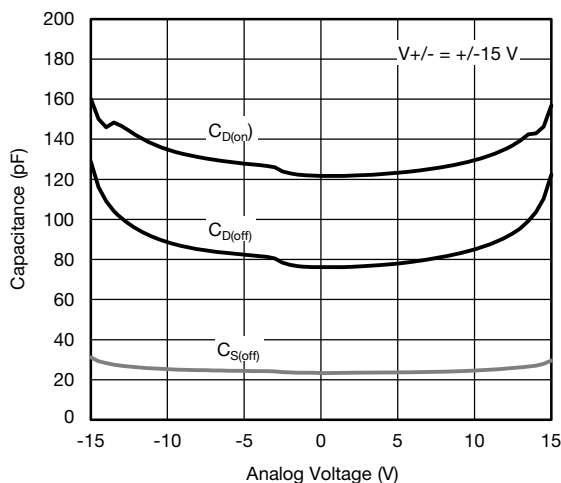
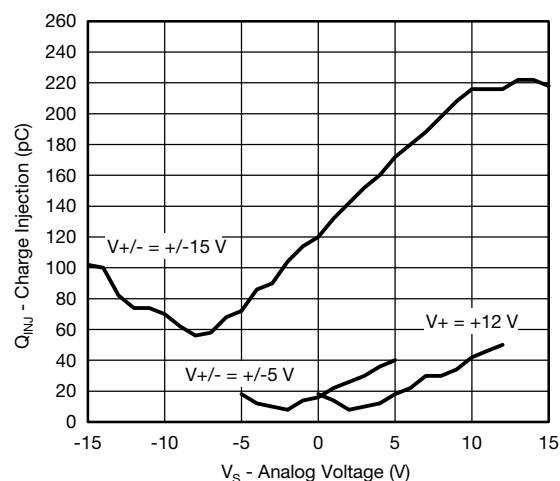
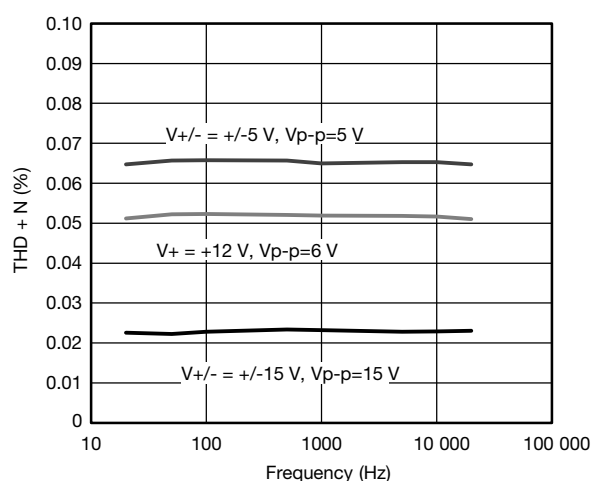
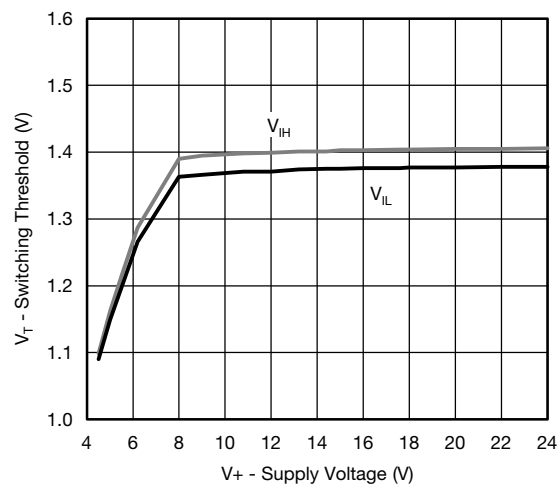
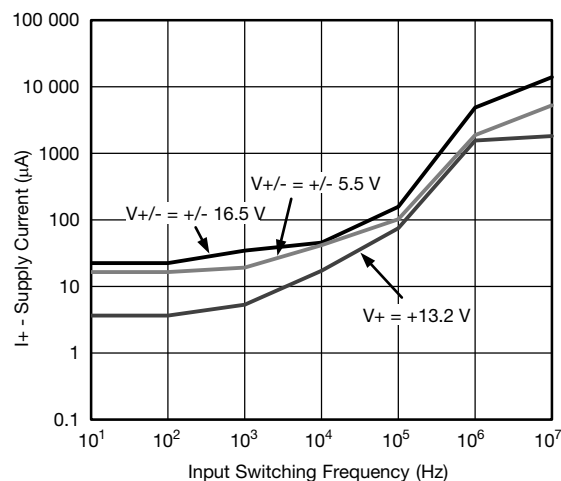
Leakage Current vs. Analog Voltage

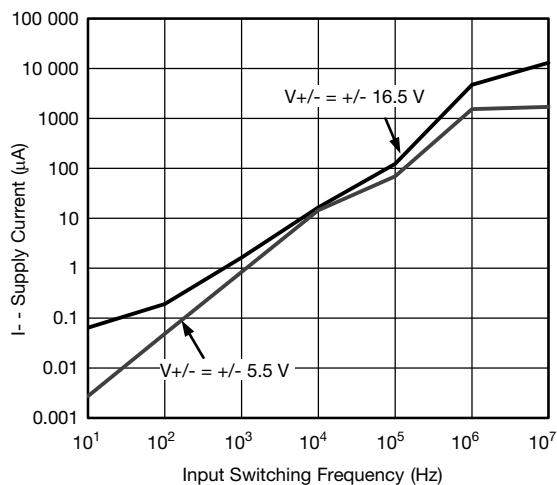
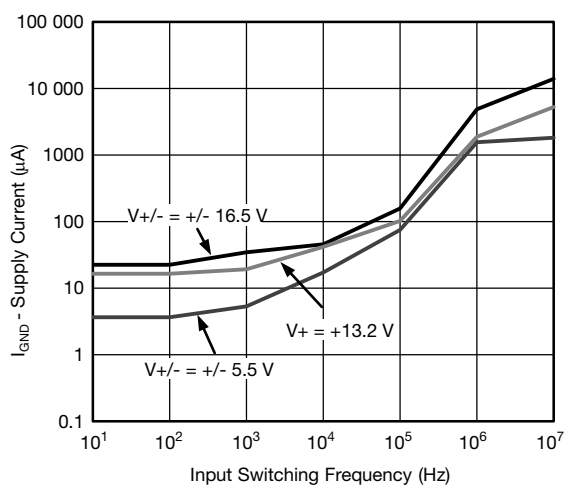
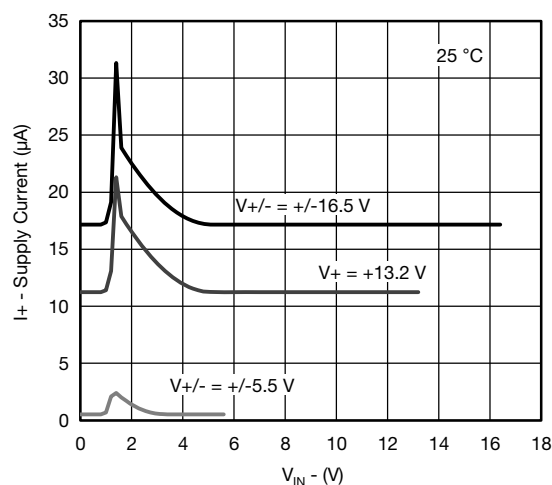


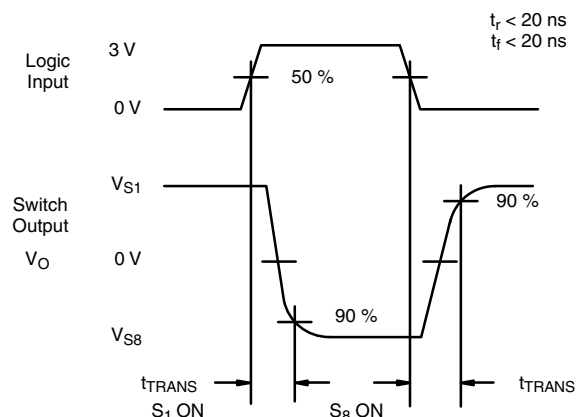
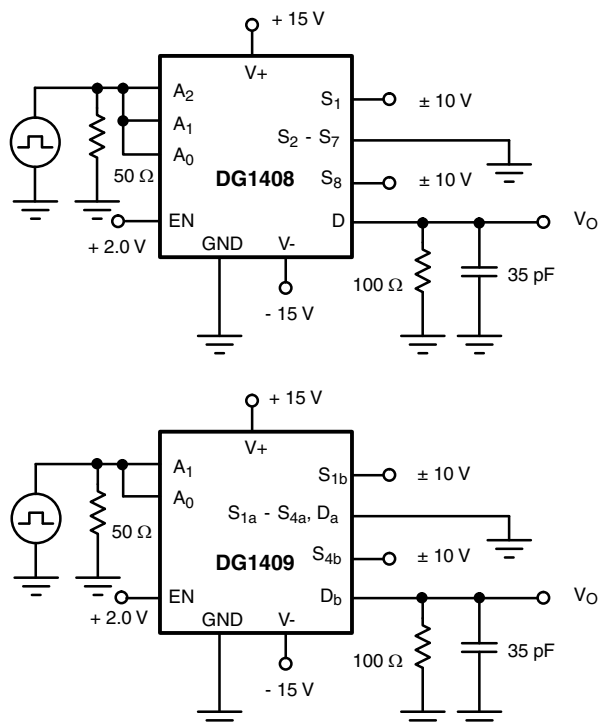
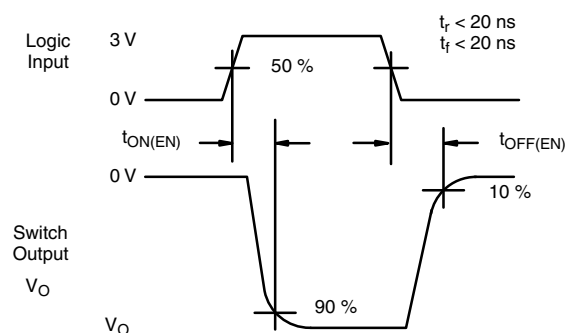
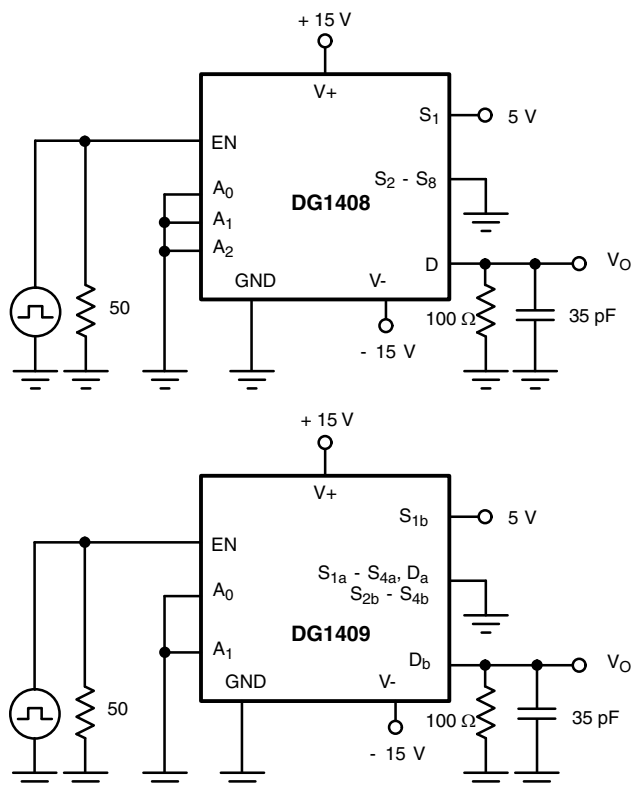
Leakage Current vs. Analog Voltage

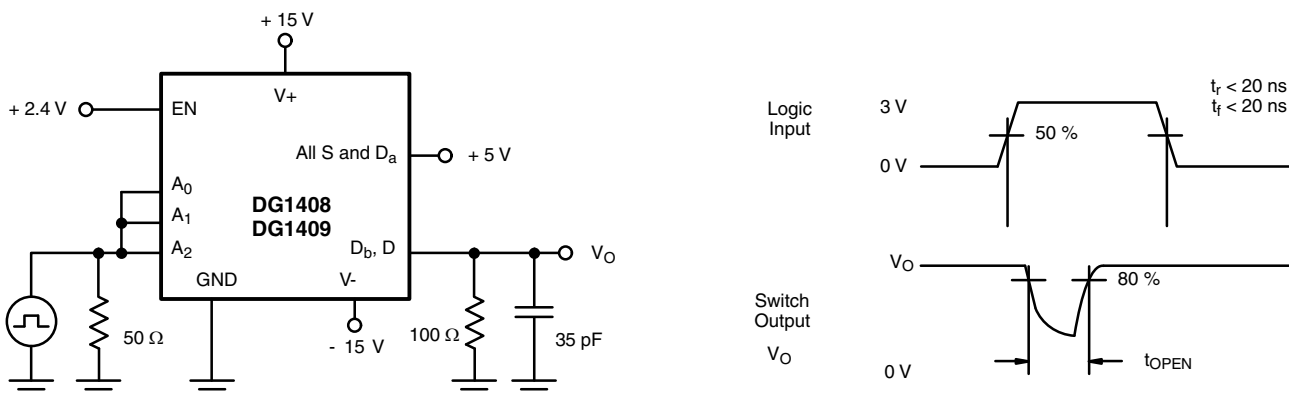
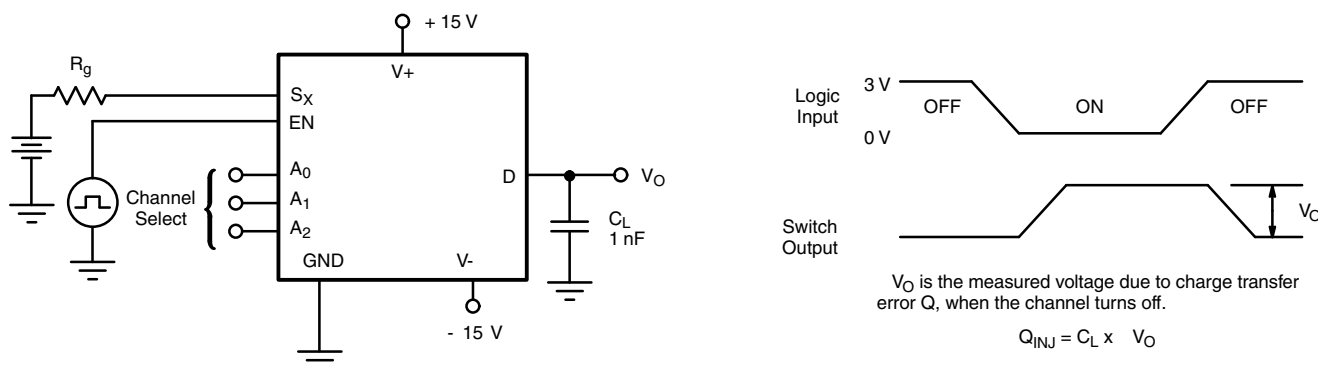
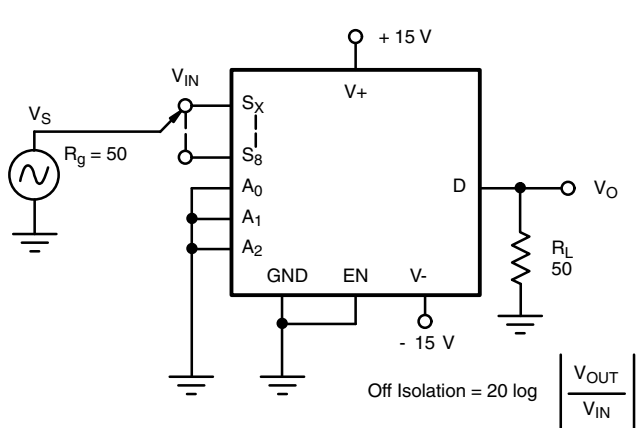
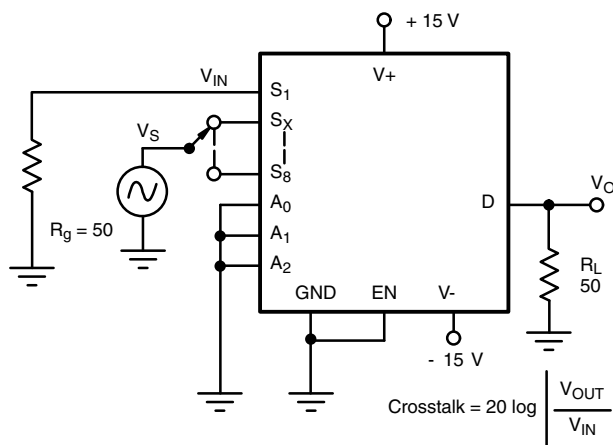


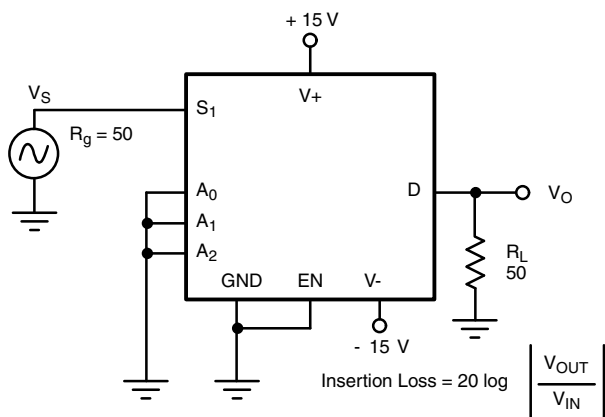
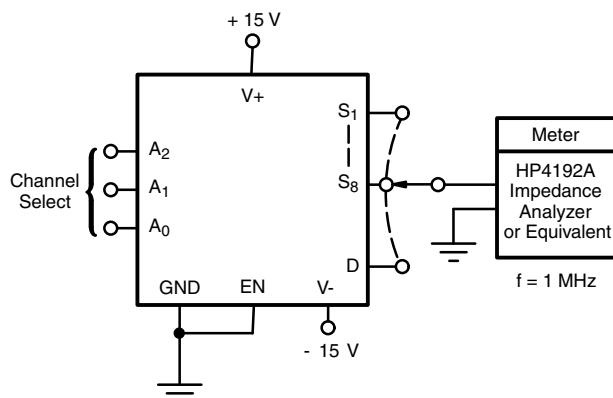
Switching Time vs. Temperature

TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Loss, OIRR, X_{TALK} vs. Frequency

Capacitance vs. Analog Voltage

Charge Injection vs. Source Voltage

THD vs. Frequency

Switching Threshold vs. Supply Voltage

Positive Supply Current vs. Switching Frequency

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Negative Supply Current vs. Switching Frequency

Ground Current vs. Switching Frequency

Positive Supply Current vs. Input Logic Voltage

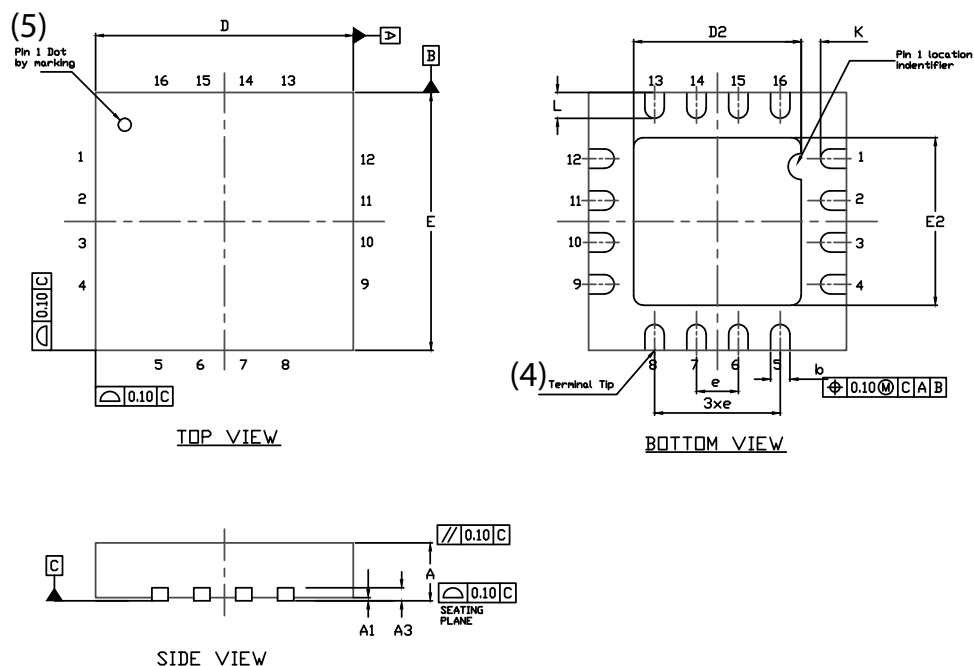
TEST CIRCUITS

Fig. 1 - Transition Time

Fig. 2 - Enable Switching Time


Fig. 3 - Break-Before-Make Internal

Fig. 4 - Charge Injection

Fig. 5 - Off-Isolation

Fig. 6 - Crosstalk


Fig. 7 - Insertion Loss

Fig. 8 - Source Drain Capacitance

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62957.

QFN 4x4-16L Case Outline



DIM	VARIATION 1						VARIATION 2					
	MILLIMETERS ⁽¹⁾			INCHES			MILLIMETERS ⁽¹⁾			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.75	0.85	0.95	0.029	0.033	0.037	0.75	0.85	0.95	0.029	0.033	0.037
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
A3	0.20 ref.			0.008 ref.			0.20 ref.			0.008 ref.		
b	0.25	0.30	0.35	0.010	0.012	0.014	0.25	0.30	0.35	0.010	0.012	0.014
D	4.00 BSC			0.157 BSC			4.00 BSC			0.157 BSC		
D2	2.0	2.1	2.2	0.079	0.083	0.087	2.5	2.6	2.7	0.098	0.102	0.106
e	0.65 BSC			0.026 BSC			0.65 BSC			0.026 BSC		
E	4.00 BSC			0.157 BSC			4.00 BSC			0.157 BSC		
E2	2.0	2.1	2.2	0.079	0.083	0.087	2.5	2.6	2.7	0.098	0.102	0.106
K	0.20 min.			0.008 min.			0.20 min.			0.008 min.		
L	0.5	0.6	0.7	0.020	0.024	0.028	0.3	0.4	0.5	0.012	0.016	0.020
N ⁽³⁾	16			16			16			16		
Nd ⁽³⁾	4			4			4			4		
Ne ⁽³⁾	4			4			4			4		

Notes

- (1) Use millimeters as the primary measurement.
- (2) Dimensioning and tolerances conform to ASME Y14.5M. - 1994.
- (3) N is the number of terminals. Nd and Ne is the number of terminals in each D and E site respectively.
- (4) Dimensions b applies to plated terminal and is measured between 0.15 mm and 0.30 mm from terminal tip.
- (5) The pin 1 identifier must be existed on the top surface of the package by using identification mark or other feature of package body.
- (6) Package warpage max. 0.05 mm.

ECN: S13-0893-Rev. B, 22-Apr-13
DWG: 5890



Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.